SONY

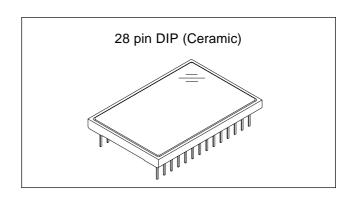
ICX263AL

Diagonal 28.42mm (Type 1.8) Frame Readout CCD Image Sensor with Square Pixel Preliminary

Description

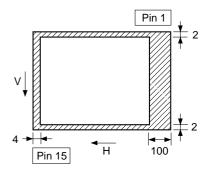
The ICX263AL is a diagonal 28.42mm (Type 1.8) image size interline CCD solid-state image sensor with a square pixel array and 10.66M effective pixels. This chip can support an output data rate up to 20MHz (max.) and a frame rate of approximately 1.6 frames/second.

This chip uses the frame readout method and features an electronic shutter with variable charge-storage time. In addition, high frame rate readout mode is also supported. Further, high sensitivity and low dark current are achieved through the adoption of HAD (Hole Accumulation Diode) sensors.



Features

- · Frame readout method
- · High horizontal and vertical resolution
- Square pixel
- Maximum output data rate: 20MHz (frame rate: approximately 1.6)
- Maximum horizontal drive frequency: 20MHz
- Supports high frame rate readout mode (effective 441 lines output)
- Reset gate voltage not adjusted
- · High sensitivity, low dark current
- Continuous variable-speed electronic shutter



Optical black position (Top View)

Device Structure

• Interline CCD image sensor

• Image size: Diagonal 28.42mm (Type 1.8)

• Total number of pixels: 4128 (H) \times 2652 (V) approx. 10.95M pixels • Number of effective pixels: 4024 (H) \times 2648 (V) approx. 10.66M pixels • Number of active pixels: 4000 (H) \times 2624 (V) approx. 10.50M pixels

• Chip size: 25.20mm (H) \times 17.96mm (V) • Unit cell size: 5.9 μ m (H) \times 5.9 μ m (V)

• Optical black: Horizontal (H) direction: Front 4 pixels, rear 100 pixels

Vertical (V) direction: Front 2 pixels, rear 2 pixels

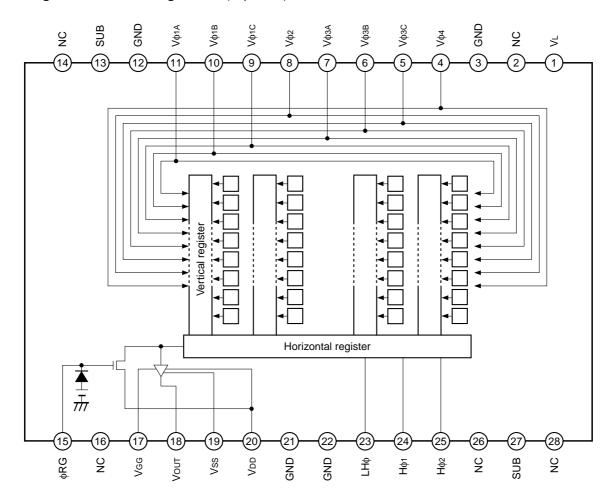
• Number of dummy bits: Horizontal 20

Vertical 1

• Substrate material: Silicon

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Block Diagram and Pin Configuration (Top View)



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	VL	Protective transistor bias	15	φRG	Reset gate clock
2	NC		16	NC	
3	GND	GND	17	Vgg	Output amplifier gate
4	Vф4	Vertical register transfer clock	18	Vouт	Signal output
5	Vфзс	Vertical register transfer clock	19	Vss	Output amplifier source
6	Vфзв	Vertical register transfer clock	20	VDD	Supply voltage
7	VфзA	Vertical register transfer clock	21	GND	GND
8	Vф2	Vertical register transfer clock	22	GND	GND
9	Vф1C	Vertical register transfer clock	23	LΗφ	Horizontal register final stage transfer clock
10	Vф1B	Vertical register transfer clock	24	Нф1	Horizontal register transfer clock
11	Vф1A	Vertical register transfer clock	25	Нф2	Horizontal register transfer clock
12	GND	GND	26	NC	
13	SUB	Substrate (overflow drain)	27	SUB	Substrate (overflow drain)
14	NC		28	NC	

Absolute Maximum Ratings

	Rating	Unit	Remarks	
	Vdd, Vout, фRG – SUB	-40 to +10	V	
Against CLID	Vφ1Α, Vφ1Β, Vφ1C, Vφ3Α, Vφ3Β, Vφ3C – SUB	-50 to +15	V	
Against SUB	$V\phi_2, V\phi_4, V_L - SUB$	-50 to +0.3	V	
	Hφ1, Hφ2, LHφ, GND – SUB	-40 to +0.3	V	
	Vdd, Vout, фRG – GND	-0.3 to +18	V	
Against CND	Vφ1Α, Vφ1Β, Vφ1C, Vφ3Α, Vφ3Β, Vφ3C – GND	-10 to +18	V	
Against GND	Vφ2, Vφ4, VL – GND	-10 to +18	V	
	Hφ1, Hφ2, LHφ – GND	-10 to +7	V	
Against \/	Vφ1Α, Vφ1Β, Vφ1C, Vφ3Α, Vφ3Β, Vφ3C – VL	-0.3 to +28	V	
Against V∟	Vφ2, Vφ4, Hφ1, Hφ2, LHφ, GND – VL	-0.3 to +17	V	
	Voltage difference between vertical clock input pins	to +15	V	*1
Between input clock pins	Hφ1 – Hφ2	-7 to +7	V	
l clock pillo	Hφ1, Hφ2 – Vφ4	-17 to +17	V	
Storage temperatur	re	-30 to +80	°C	
Guaranteed temper	rature of performance	-10 to +60	°C	
Operating temperat	ture	-10 to +75	°C	

 $^{^{*1}}$ +27V (Max.) is guaranteed when clock width < 10 μ s, clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage	VDD	14.55	15.0	15.45	V	
Output amplifier gate voltage	Vgg	5.5	6.0	6.5	V	
Output amplifier source	Vss	Connected to GND via resistance of 200 to 600Ω				
Substrate voltage adjustment range	VsuB	8.5	8.5 15.0			
Protective transistor bias	VL					
Reset gate clock	φRG					

^{*2} VL setting is the VvL voltage of the vertical clock waveform, or the same voltage as the VL power supply for the V driver should be used.

DC characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		8.7		mA	

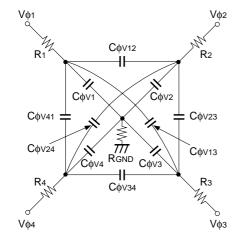
^{*3} Do not apply a DC bias to the reset gate clock pin, because a DC bias is generated within the CCD.

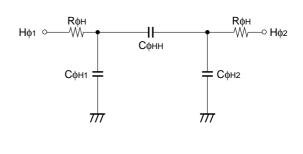
Clock Voltage Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Readout clock voltage	VvT	14.55	15.0	15.45	V	
Vertical transfer clock	Vvн	-0.05	0	0.05	V	
voltage	VvL	-9.5	-9.0	-8.5	V	
Horizontal transfer clock	Vфн	6.0			V	Absolute maximum voltage value ≤ 8.0V
voltage	VHL	-0.25	0	0.25	V	
Horizontal final stage	VLHH	7.6	8.0	8.4	V	
transfer clock voltage	VLHL	-2.25	-2.0	-1.75	V	
Reset gate clock voltage	Vørg	4.5	5.0	5.5	V	
Substrate clock voltage	Vфsuв	23.05	24.0	24.95	V	

Clock Equivalent Circuit Constants

Item	Symbol	Тур.	Unit	Remarks
Canaditanas hatusan vertical transfer alask and CND	Сфу1, Сфуз	21000	pF	
Capacitance between vertical transfer clock and GND	Сф∨2, Сф∨4	12000	pF	
	Сф∨12, Сф∨34	8500	pF	
Conscitores hatus or vertical transfer alocks	Сф∨23, Сф∨41	7100	pF	
Capacitance between vertical transfer clocks	Сф∨13	3100	pF	
	Сф∨24	1700	pF	
Conscitores between beginning to transfer cleak and CND	Сфн1	230	pF	
Capacitance between horizontal transfer clock and GND	Сфн2	180	pF	
Capacitance between horizontal transfer clocks	Сфнн	300	pF	
Capacitance between horizontal final stage transfer clock and GND	Сфін	8	pF	
Capacitance between reset gate clock and GND	Сфяс	6	pF	
Capacitance between substrate clock and GND	Сфѕив	4700	pF	
Vertical transfer clock series resistor	R1, R2, R3, R4	20	Ω	
Vertical transfer clock ground resistor	RGND	30	Ω	
Horizontal transfer clock series resistor	Rфн	0.6	Ω	



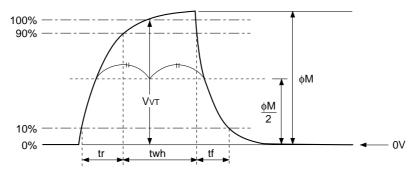


Vertical transfer clock equivalent circuit

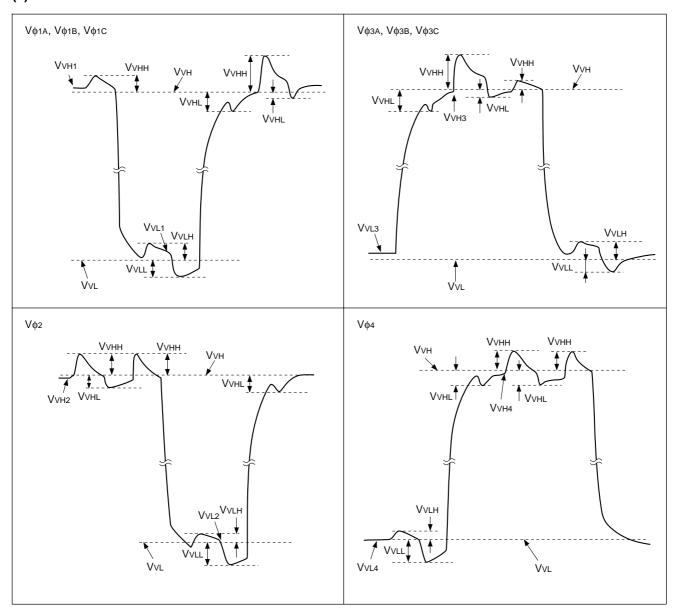
Horizontal transfer clock equivalent circuit

Drive Clock Waveform Conditions

(1) Readout clock waveform



(2) Vertical transfer clock waveform

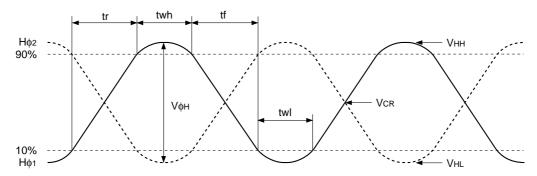


VvH = (VvH1 + VvH2)/2

 $V \lor L = (V \lor L3 + V \lor L4)/2$

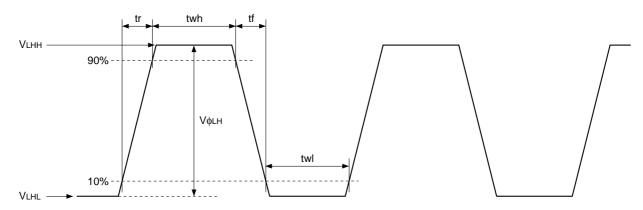
 $V\phi v = Vvhn - Vvhn (n = 1 to 4)$

(3) Horizontal transfer clock waveform

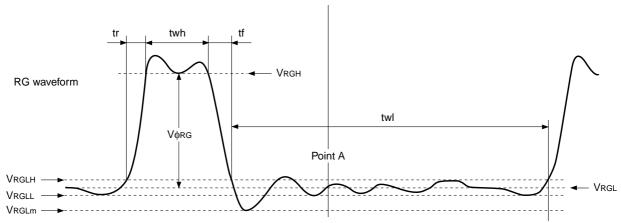


Cross-point voltage for the $H\phi_1$ rising side of the horizontal transfer clocks $H\phi_1$ and $H\phi_2$ waveforms is VcR.

(4) Horizontal final stage transfer clock waveform



(5) Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG.

In addition, VRGL is the average value of VRGLH and VRGLL.

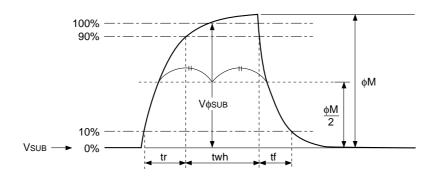
$$V_{RGL} = (V_{RGLH} + V_{RGLL})/2$$

Assuming VRGH is the minimum value during the interval twh, then:

$$V \phi RG = V RGH - V RGL$$

Negative overshoot level during the falling edge of RG is VRGLm.

(6) Substrate clock waveform



Clock Switching Characteristics

lt o mo	Oaala ad	twh		twl		tr		tf			1.1.4	Damarka			
Item	Symbol	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Min.	Тур.	Мах.	Unit	Remarks
Readout clock	VT		5.5						1.5			1.5		μs	During readout
Vertical transfer clock	Vф1A, Vф1B, Vф1C, Vф2, Vф3A, Vф3B, Vф3C, Vф4								2			2		μs	When using CXD1268M
Horizontal transfer clock	Н ф1, Н ф2		17			17			8			8		ns	
Horizontal final stage transfer clock	LHφ		22			22			3			3		ns	*1
Reset gate clock	φRG		7						2.5			2.5		ns	
Substrate clock	φSUB		3.0											μs	During drain charge

^{*1} Be sure to match the phases of the amplitude level 50% of the horizontal final stage transfer clock and the amplitude level 50% of horizontal transfer clock $H_{\phi 2}$.

Image Sensor Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity	s	320	400		mV	1	1/60s accumulation, F5.6
Saturation signal	Vsat	500			mV	2	Ta = 60°C
Smear	Sm		0.001	0.003	%	3	No electronic shutter
Vide e signal abadin e*1	Ch			20	%	4	Zone I
Video signal shading*1	Sh			25	%	4	Zone II
Dark signal	Vdt			17	mV	5	Ta = 60°C, 1.6 frame/s
Dark signal shading	ΔVdt			28	mV	6	Ta = 60°C, 1.6 frame/s
Lag	Lag			0.5	%	7	
Maximum frame rate				1.6	/s		Horizontal drive frequency: 20MHz

^{*1} Video signal shading is the value with parallel incident light and a lens aperture value of F5.6 to F8.

O Zone Definition of Video Signal Shading

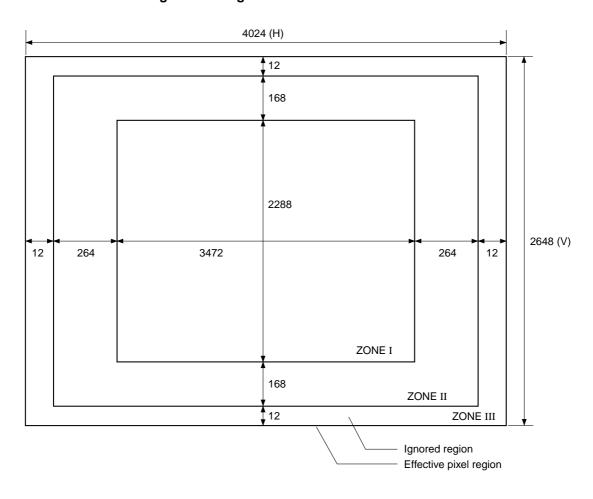


Image Sensor Characteristics Measurement Method

Measurement conditions

(1) In the following measurements, the device drive conditions are at the typical values of the bias and clock voltage conditions, and the frame readout mode is used.

(2) In the following measurements, spot blemishes are excluded and, unless otherwise specified, the optical black level (OB) is used as the reference for the signal output, which is taken as the value measured at the output point (CCD OUT) shown in the drive circuit.

Definition of standard imaging conditions

(1) Standard imaging condition I:

Use a pattern box (luminance: 706cd/m^2 , color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F5.6. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

(2) Standard imaging condition II:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity

Set to standard imaging condition I. After setting the electronic shutter mode with a shutter speed of 1/60s, measure the signal output at the center of the screen.

2. Saturation signal

Set to standard imaging condition II. After adjusting the luminous intensity to 20 times the intensity with the average value of the signal output, 150mV, measure the minimum value of the signal output.

3. Smear

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, first adjust the luminous intensity to 500 times the intensity with the average value of signal output, 150mV. After the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (Vsm [mV]) of the signal output and substitute the value into the following formula.

Sm =
$$\frac{\text{Vsm}}{150} \times \frac{1}{500} \times \frac{1}{10} \times 100$$
 [%] (1/10V method conversion value)

4. Video signal shading

Set to standard imaging condition II. With the lens diaphragm at F5.6 to F8, input parallel light with an exit pupil distance of near infinity to the CCD image surface and adjust the luminous intensity so that the average value of the signal output is 150mV. Then measure the maximum value (Vmax [mV]) and minimum value (Vmin [mV]) of the signal output and substitute the values into the following formula.

$$Sh = (Vmax - Vmin)/150 \times 100 [\%]$$

5. Dark signal

Measure the average value of the signal output (Vdt [mV]) with the device ambient temperature 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as a reference.

6. Dark signal shading

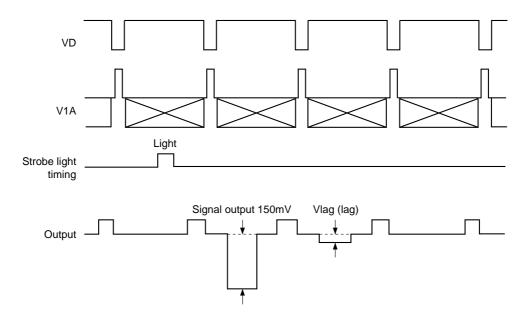
After measuring 5, measure the maximum (Vdmax [mV]) and minimum (Vdmin [mV]) values of the dark signal output and substitute the values into the following formula.

$$\Delta Vdt = Vdmax - Vdmin [mV]$$

7. Lag

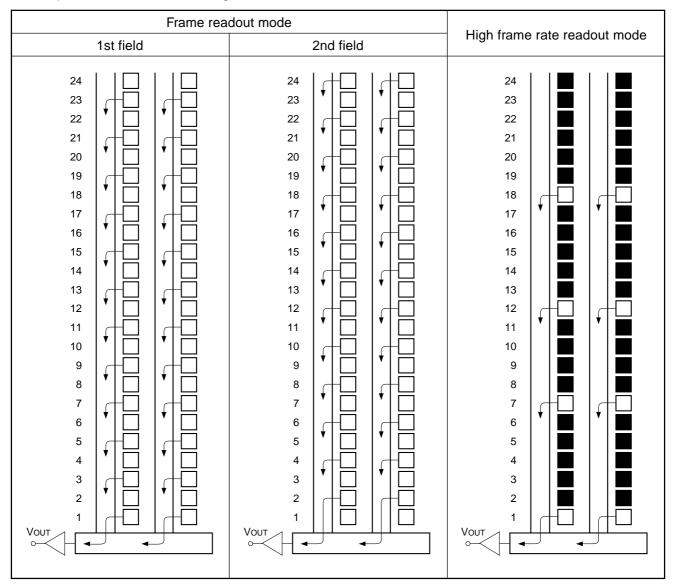
Adjust the signal output generated by strobe light to 150mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal (Vlag). Substitute the value into the following formula.

$$Lag = (Vlag/150) \times 100 [\%]$$



Readout modes

The output methods for the following two readout modes are shown below.



Note) Blacked out portions in the diagram indicate pixels which are not read out.

Output starts from line 1 in high frame rate readout mode.

1. Frame readout mode

In this mode, all pixel signals are divided into two fields and output.

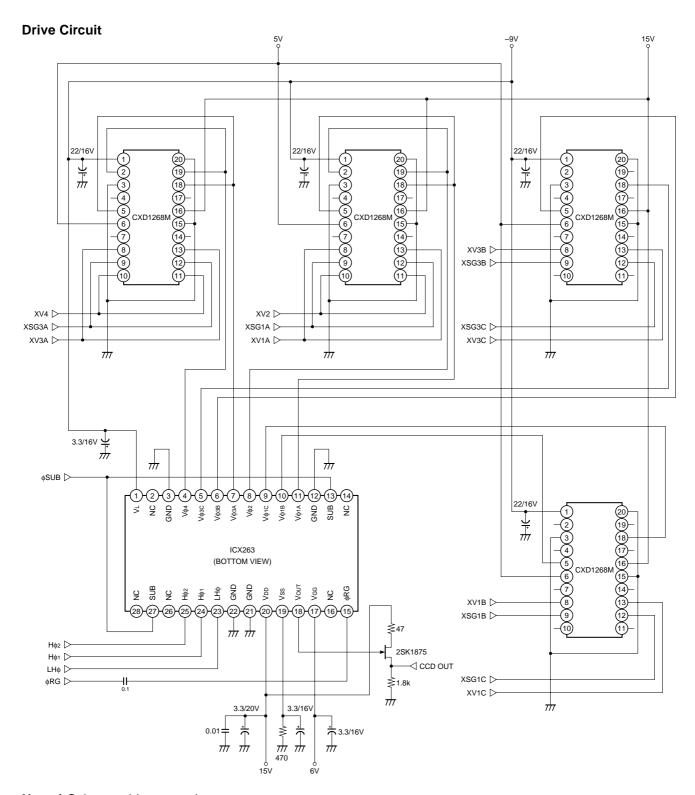
All pixel signals are read out independently, making this mode suitable for high resolution image capturing.

2. High frame rate readout mode

Output is performed at approximately 9 frames/s by reading out 4 out of 24 vertical pixels.

The number of output lines is 441 lines.

This readout mode emphasizes processing speed over vertical resolution.



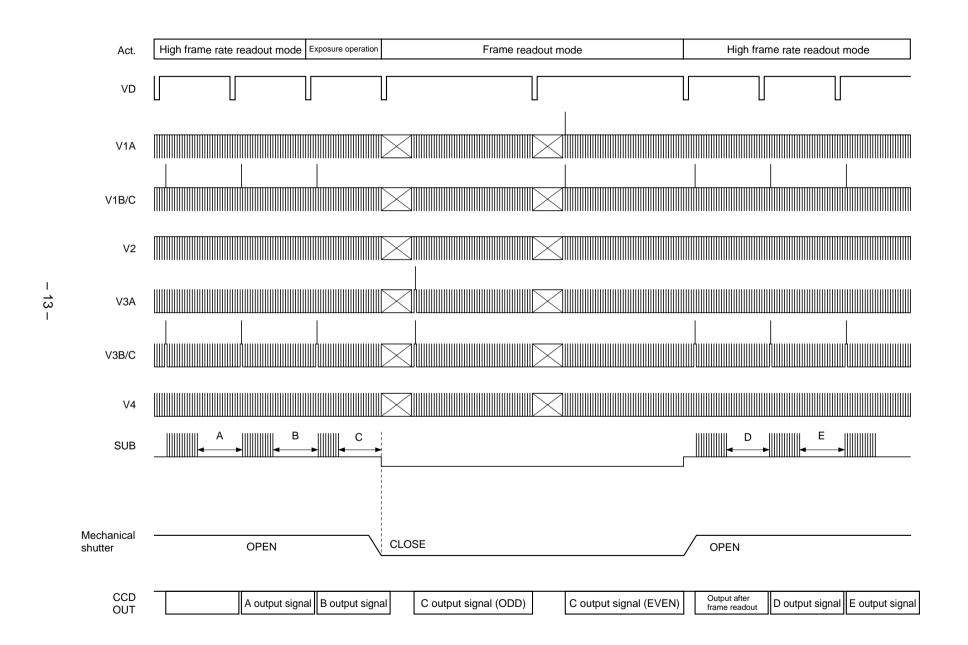
Notes) Substrate bias control

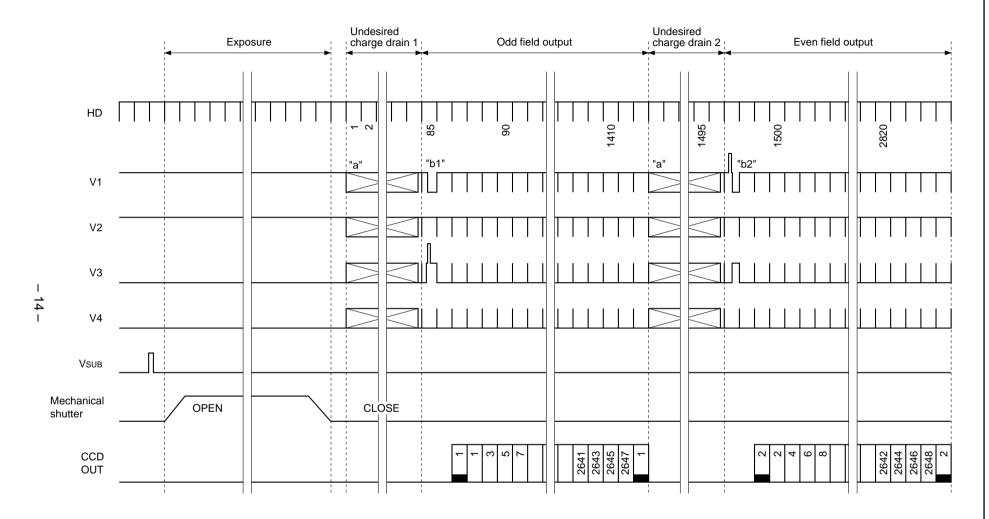
The saturation signal level decreases when exposure is performed using the mechanical shutter, so control the substrate bias.

Drive timing precautions

The blooming signal generated during exposure in mechanical shutter mode is swept by providing two fields of idle transfer through vertical register high-speed sweep transfer from the time the mechanical shutter closes until sensor readout is performed. However, note that the V_L potential and the ϕSUB pin DC voltage sag at this time.

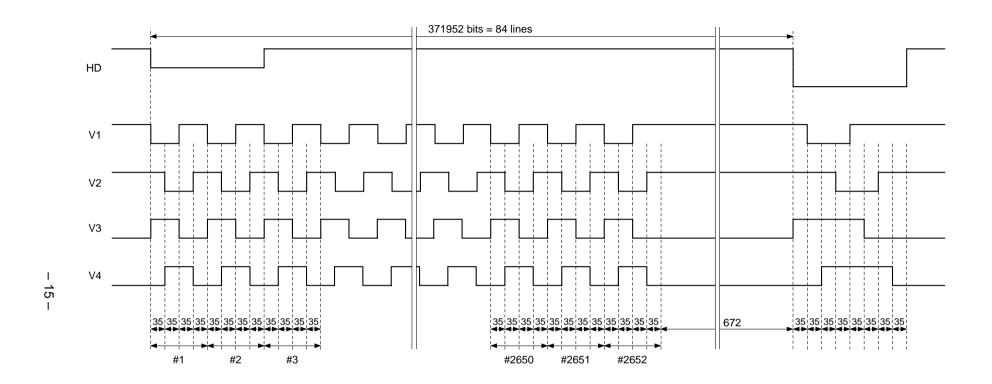
Drive Timing Chart (Vertical Sequence) High Frame Rate Readout Mode → Frame Readout Mode/Electronic Shutter Normal Operation



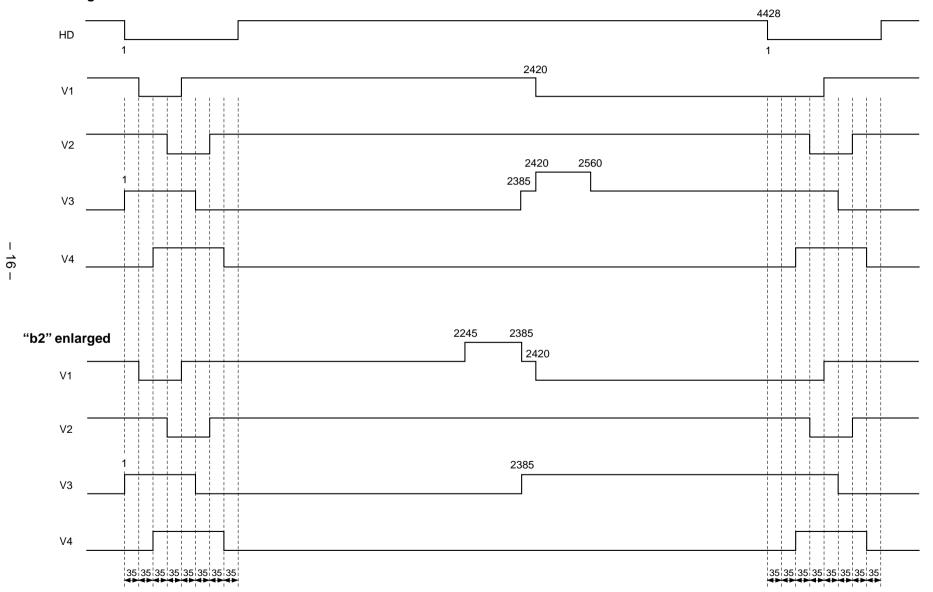


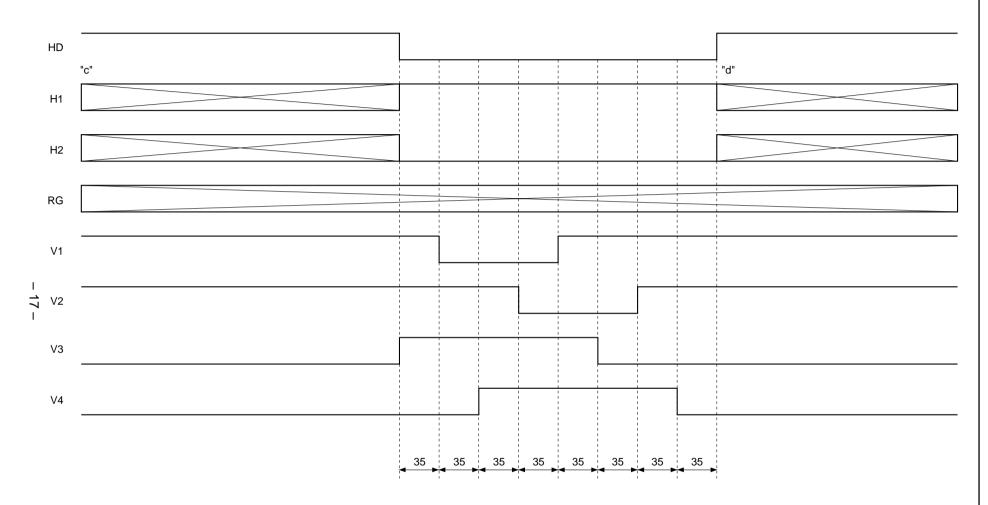
Note) Number of effective vertical pixels: 2648 (1 frame), number of vertical optical black pixels: front 2, rear 2 (1 frame)

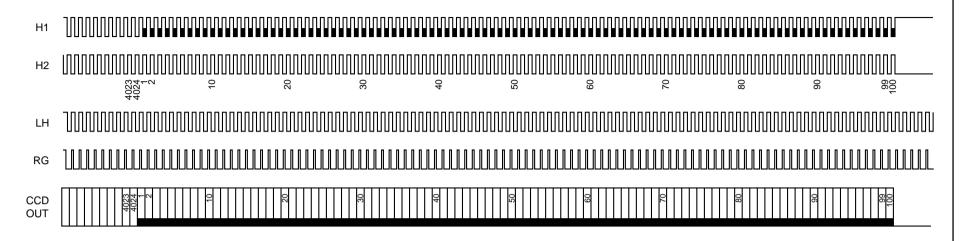
Drive Timing Chart (Vertical Sync "a" Enlarged, Undesired Charge Drain)



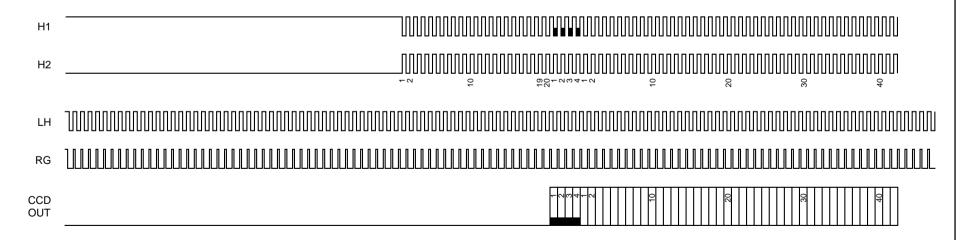








 $\stackrel{
ightharpoonup}{\infty}$ Drive Timing Chart (Horizontal Sync "d" Enlarged)

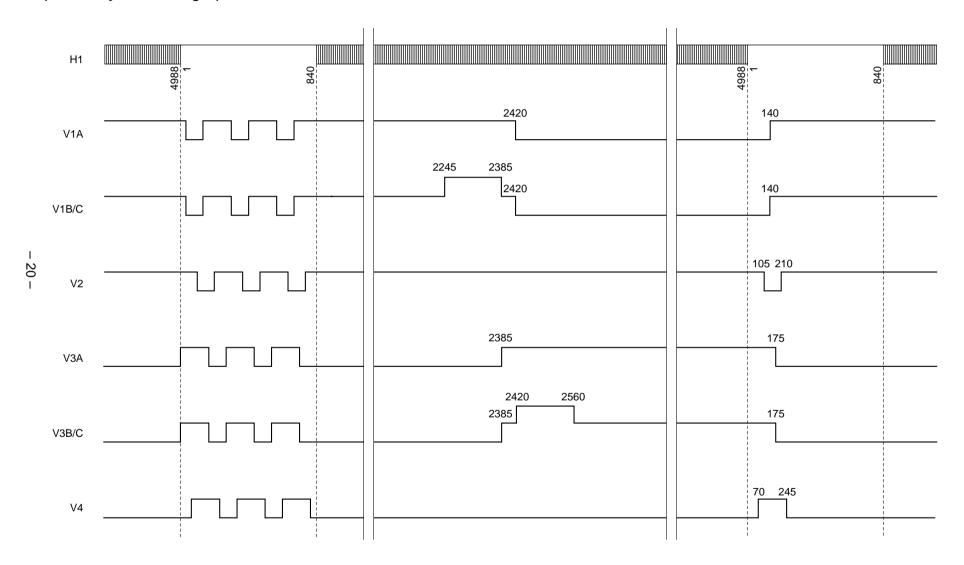


2593 2599 2604 2610 2617 2623 2628 2634 2641 2647	V3B/C	V2	V1B/C	339 440 441 442 443 444 445 446
1 7 12 18 25 31 36 42				• 1 2 3 3 4 4 5 5 6 6 5 6 5 6 5 6 5 6 5 6 6 5 6 6 5 6
2593 2599 2604 2610 2617 2623 2628 2634 2641 2647				339 440 441 442 443 444 445 446
1 7 12 18 25 31 36 42				φ ₁ 1 2 3 3 4 5 5 6 6

Drive Timing Chart (Vertical Sync) High Frame Rate Readout Mode

ICXSe3PL

(Vertical Sync "e" Enlarged)



Notes on Handling

1) Static charge prevention

CCD image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- a) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- b) When handling directly use an earth band.
- c) Install a conductive mat on the floor or working table to prevent the generation of static electricity.
- d) Ionized air is recommended for discharge when handling CCD image sensor.
- e) For the shipment of mounted substrates, use boxes treated for the prevention of static charges.

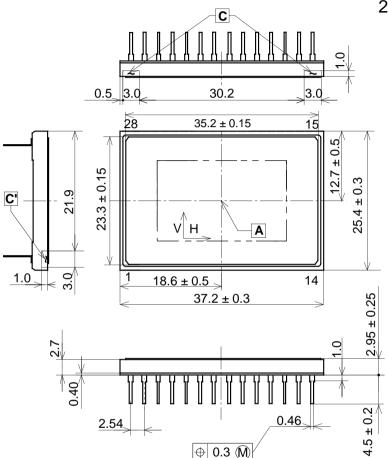
2) Soldering

- a) Make sure the package temperature does not exceed 80°C.
- b) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a ground 30W soldering iron and solder each pin in less than 2 seconds. For repairs and remount, cool sufficiently.
- c) To dismount an image sensor, do not use a solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero cross On/Off type and connect it to ground.

3) Dust and dirt protection

Image sensors are packed and delivered by taking care of protecting its glass plates from harmful dust and dirt. Clean glass plates with the following operation as required, and use them.

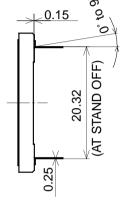
- a) Operate in clean environments (around class 1000 is appropriate).
- b) Do not either touch glass plates by hand or have any object come in contact with glass surfaces. Should dirt stick to a glass surface, blow it off with an air blower. (For dirt stuck through static electricity ionized air is recommended.)
- c) Clean with a cotton bud and ethyl alcohol if the grease stained. Be careful not to scratch the glass.
- d) Keep in a case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- e) When a protective tape is applied before shipping, just before use remove the tape applied for electrostatic protection. Do not reuse the tape.
- 4) Do not expose to strong light (sun rays) for long periods.
- 5) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or usage in such conditions.
- 6) CCD image sensors are precise optical equipment that should not be subject to too much mechanical shocks.

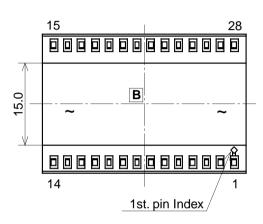


PACKAGE STRUCTURE

PACKAGE MATERIAL	Ceramic
LEAD TREATMENT	GOLD PLATING
LEAD MATERIAL	42 ALLOY
PACKAGE MASS	7.80g
DRAWING NUMBER	AS-Z3

28 pin DIP (800mil)





- 1. "A" is the center of the effective image area.
- 2. The point **"C"** of the package is the horizontal reference. The two points **"C"** of the package are the vertical reference.
- 3. The center of the effective image area relative to "C" and "C" is $(H, V) = (18.6, 12.7) \pm 0.5$ mm.
- 4. The rotation angle of the effective image area relative to "C" is $\pm 1^{\circ}$.
- 5. The height from the reference surface "B" to the effective image area is 1.55 ± 0.15 mm.
- 6. The tilt of the effective image area relative to the reference surface "B" is 200µm or less.
- 7. The adhesive must not extend past the cover glass surface.
- 8. The thickness of the cover glass is 0.75mm (actual dimension), and the refractive index is 1.5.